## **EUROPEAN PATENT OFFICE**

## **Patent Abstracts of Japan**

PUBLICATION NUMBER

06013654

**PUBLICATION DATE** 

21-01-94

APPLICATION DATE

17-02-93

APPLICATION NUMBER

05052884

APPLICANT: SANKEN ELECTRIC CO LTD;

INVENTOR: TADA YOSHIAKI;

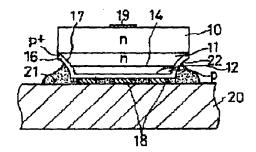
INT.CL.

: H01L 33/00 H01L 21/52 H01L 21/78

TITLE

SEMICONDUCTOR LIGHT EMITTING

**ELEMENT AND ITS MANUFACTURE** 



ABSTRACT: PURPOSE: To prevent solder from attaching by moving a p-n junction part exposed in a mesa etching side surface of a GaP light emitting diode.

> CONSTITUTION: A wafer is prepared by forming an n-type first semiconductor region 11 and a p-type second semiconductor region 12 on an n-type semiconductor substrate 10 by an epitaxial growth method. A groove is formed along a division predetermined region of a surface at the side of the second semiconductor region 12 of the wafer. Then, p-type impurities are diffused to include the groove. After an anode electrode 18 and a cathode electrode 19 are formed, a light emitting diode is acquired by cutting by the groove. It is then adhered to a metal substrate 20 by solder 21 with the anode electrode 18 down.

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